CMH65R078

650V, 59mΩ typ., 50A N-Channel Super Junction Power MOSFET

General Description

CMH65R078 is power MOSFET using Cmos's advanced super junction technology that can realize very low on-resistance and gate charge. It has low gate charge and ultra-fast body diode, so turn off action is improved. CMH60R078 provides excellent performances, such as efficiency and EMI, in soft switching applications.

Features

- Multi-layer Epitaxial Chip Technology
- Low On-Resistance
- 100% avalanche tested
- RoHS Complian

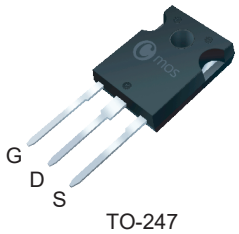
Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
650V	70mΩ	50A

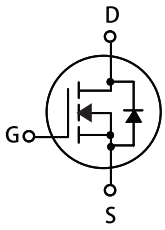
Applications

- Switching applications

TO-247 Pin Configuration



TO-247



Type	Package	Marking
CMH65R078	TO-247	CMH65R078

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	±30	V
I_D@T_C=25℃	Continuous Drain Current	50	A
I_D@T_C=100℃	Continuous Drain Current	31.6	A
I_{DM}	Pulsed Drain Current	200	A
EAS	Single Pulse Avalanche Energy[1]	600	mJ
P_D@T_C=25℃	Total Power Dissipation	266	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	150	℃

Thermal Data

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	45.1	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-case	0.47	℃/W

Electrical Characteristics (T_J=25℃ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	650	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=15A	---	59	70	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	3	---	5	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=600V , V_{GS}=0V	---	---	13	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=± 30V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=10V , I_D=15A	---	26	---	S
Q_g	Total Gate Charge	I_D=45A V_{DS} =480V V_{GS} =10V	---	88	---	nC
Q_{gs}	Gate-Source Charge		---	28	---	
Q_{gd}	Gate-Drain Charge		---	35	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS} =300V V_{GS} =10V I_D=45A R_G=2Ω	---	33	---	ns
T_r	Rise Time		---	160	---	
$T_{d(off)}$	Turn-Off Delay Time		---	76	---	
T_f	Fall Time		---	5	---	
C_{iss}	Input Capacitance	V_{DS}=100V , V_{GS}=0V , f=1MHz	---	3600	---	pF
C_{oss}	Output Capacitance		---	150	---	
C_{rss}	Reverse Transfer Capacitance		---	5	---	

Diode Characteristics

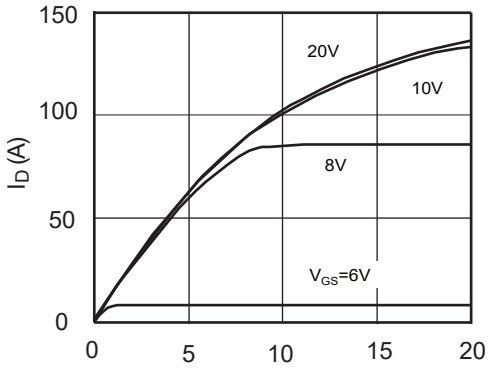
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	50	A
I_{SM}	Pulsed Source Current		---	---	200	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=30A	---	0.9	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS}=0V , I_S=50A	---	280	---	ns
Q_{rr}	Reverse Recovery Charge	dI_F/dt =100A/μs	---	2.69	---	μC

Notes:

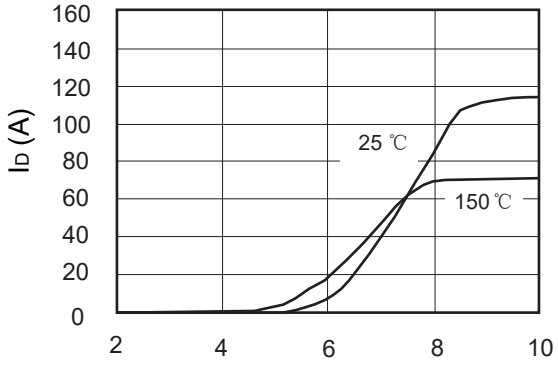
1.The EAS data shows Max. rating .The test condition is V_{DS}=50V , V_{GS}=10V , L=5mH , I_{AS}=15.5A.

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Cmos reserver the right to improve product design ,functions and reliability wihtout notice.Please refer to the latest version of specification.

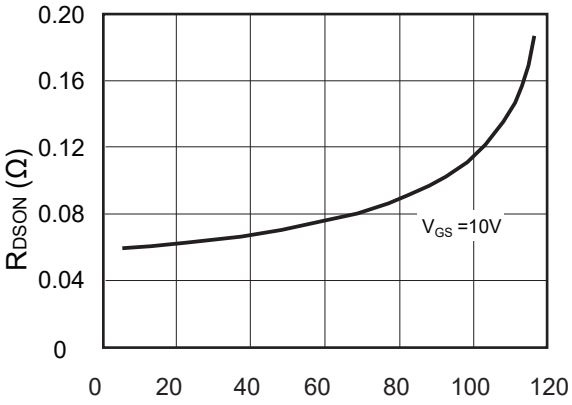
Typical Characteristics



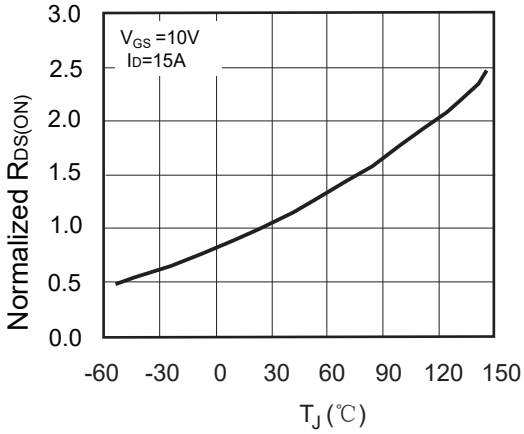
Output Characteristics



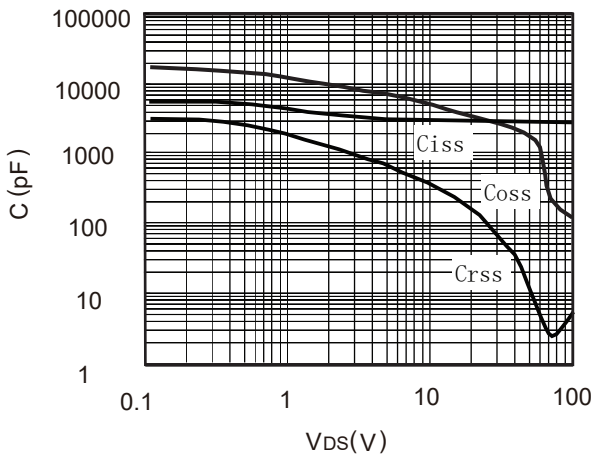
transfer characteristics



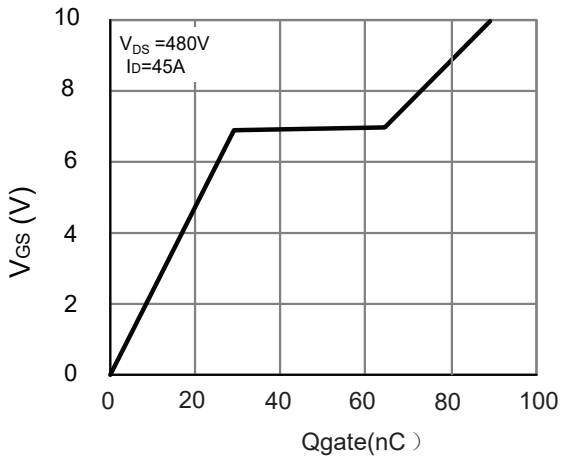
drain-source on-resistance



On-Resistance vs. Junction Temperature

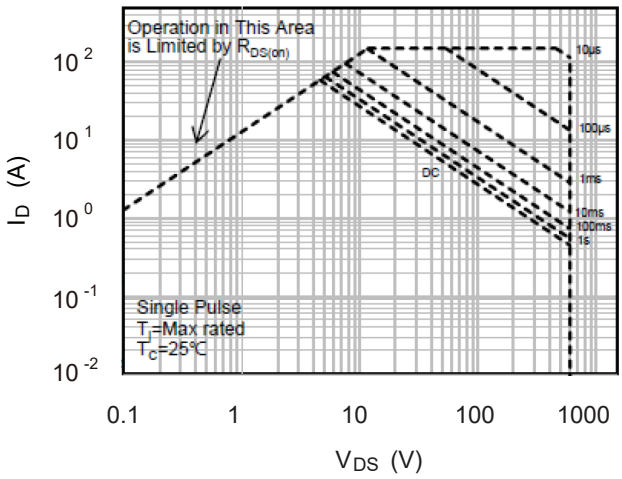


Capacitance Characteristics

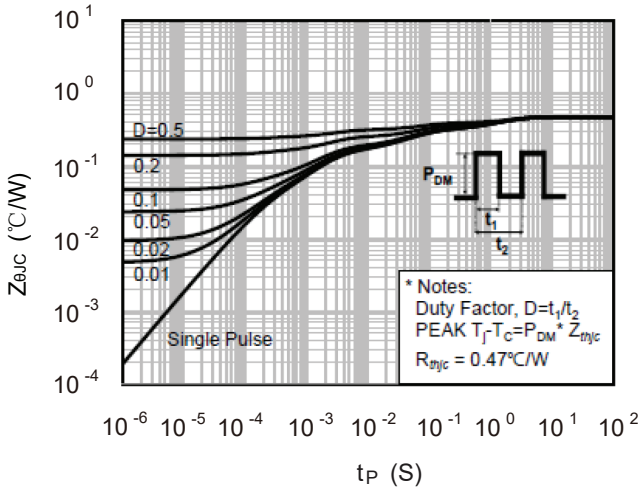


Gate charge vs gate-source voltage

Typical Characteristics



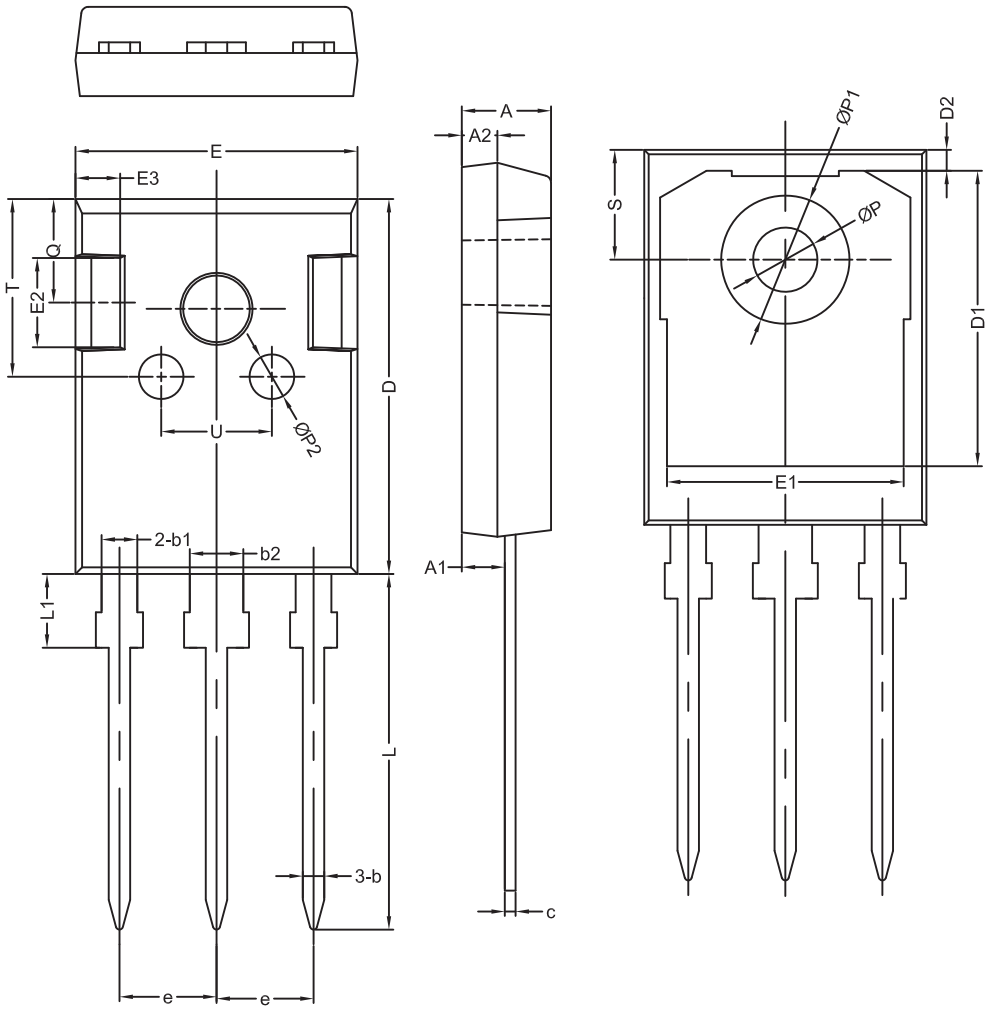
Safe Operating Area



Transient thermal impedance

Package Dimension

TO-247 Unit :mm



符号	机械尺寸/mm			符号	机械尺寸/mm		
	最小值	典型值	最大值		最小值	典型值	最大值
A	4.80	5.00	5.20	E2		5.00	
A1	2.21	2.41	2.61	E3		2.50	
A2	1.90	2.00	2.10	e		5.44	
b	1.10	1.20	1.35	L	19.42	19.92	20.42
b1		2.00		L1		4.13	
b2		3.00		P	3.50	3.60	3.70
c	0.55	0.60	0.75	P1		7.19	
D	20.80	21.00	21.20	P2		2.50	
D1		16.55		Q		5.80	
D2		1.20		S	6.05	6.15	6.25
E	15.60	15.80	16.0	T		10.00	
E1		13.30		U		6.20	